

a pressure detecting means provided inside said upper electrode, wherein operation of said parallel-plate dry-etching apparatus ceases if a pressure measured by

133  
25 said pressure detecting means is lower than a predetermined value.

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5. **(Twice Amended)** An apparatus for manufacturing a semiconductor device, comprising:

134 an upper electrode that supplies gas in a parallel-plate dry etching apparatus;

a first pressure detecting means provided inside of said upper electrode;

a second pressure detecting means provided within said dry etching apparatus in which a wafer is placed; and

a detecting means which measures a pressure differential between respective pressures of said first and said second pressure detecting means, and upon reaching a predetermined pressure differential, operation of the apparatus is terminated.

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### REMARKS

#### *Status of the Claims*

Upon entry of the present amendment, claims 1-9 will be pending in this application. Claims 3 and 5 are the independent claims.

#### *Objection to the Drawings*

The proposed amendment to Fig. 2 in red ink is believed to bring it in compliance with MPEP § 608.02(g). A similar amendment was submitted on July 15, 2002.

Apparently this was not satisfactory. In the event that the present proposed changes are